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Analysis on the Characteristics of Single-walled Carbon Nanotube Transistor Printed by Roll-to-Roll and Roll-to-Device Method

<u>윤유상</u>, Yutaka Majima, 박완준, Yasuo Azuma 한양대학교

Flexible electronics, a future technology of electronics, require a low cost integrated circuit that can be built on various types of the flexible substrates. As a potential candidate for this application, a single walled carbon nanotube network is studied as an active device with a scheme of thin film transistor. Transistors are formed on a plastic foil by the Roll-to-Roll (R2R) and the Roll-to-Device (R2D) printing method. For both printing methods, electrical transports for the transistors are presented with the temperature dependence of threshold voltage (V_Th) and mobility from the measured transfer curves at temperatures ranging from 10 K to 300 K.

It is observed that μ =0.044cm²/V · sec and V_Th=7.28V for R2R and μ =0.025cm²/V · sec and V_Th=3.10V for R2D, both for the temperature at 300K. Temperature dependence of mobility and V_Th is observed. However for R2R, the temperature dependence of V_Th is constant. It is the difference between, R2R and R2D.

Keywords: carbon nanotube, temperature characteristics

